

PSICSD2P1200V20N

Schoktty Barrier Diode

Feature

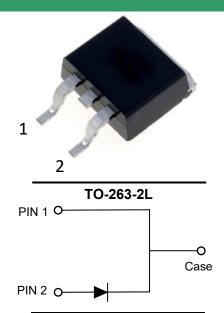
- Low conduction loss due to low V_F
- Extremely low switching loss by tiny Q_C
- Negligible reverse recovery
- Positive Temperature Coefficient
- Pb-free / RoHS compliant
- > Highly rugged due to better surge current
- ➤ High-reliability

Applications

- Solar inverters
- Uninterruptable power supplies
- Motor drives
- Power Factor Correction

Absolute maximum rating@25°C

Parameter			Value	Units
Repetitive Peak Reverse Voltage		V _{RRM}	1200	V
Surge Peak Reverse Voltage		V _{RSM}	1200	V
DC Peak Reverse Voltage		V _R	1200	V
Continuous Forward Current	T _c =25℃		54	A
	T _c =135°C	I _F	27	
	T _c =153°C		20	
Repetitive Peak Forward Surge Current	T _c =25°C,t _p =10ms,Half Sine Pulse		86	A
	T _c =110°C,t _p =10ms,Half Sine Pulse	I _{FRM}	58	
Non-repetitive Forward Surge Current	T _c =25°C,t _p =10ms,Half Sine Pulse		160	A
	T _c =110°C,t _p =10ms,Half Sine Pulse	I _{FSM}	130	
i ² dt value	T _c =25°C,t _p =10ms,Half Sine Pulse	(:2-14	128	A ² s
	T _c =110°C,t _p =10ms,Half Sine Pulse	∫i²dt	84	
Power Dissipation	T _c =25℃		214	w
	T _c =110°C	P _{tot}	93	
Operating junction Range		TJ	-55~+175	°C
Soldering Temperature		T _{stg}	-55~+150	°C



Circuit Diagram

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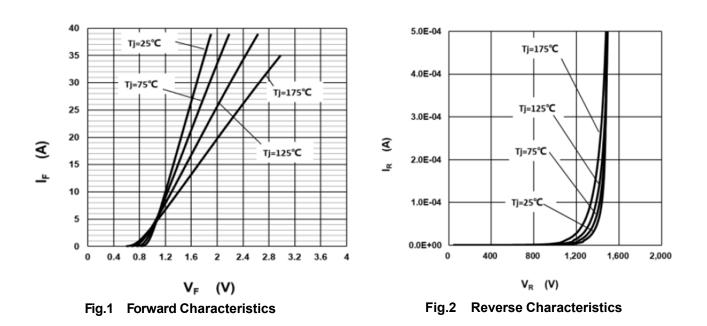
Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units	
Forward Voltage	V _F	I _F = 20A, T _J =25°C	-	1.4	1.7	V	
		Ι _F = 20Α, Τ _J =175°C	-	2.0	-		
Reverse Current	I _R	V _R = 1200V, T _J =25°C	-	-	200	μA	
		V _R = 1200V, T _J =175°C	-	-	400		
Total Capacitive Charge	Q _c	$V_{\rm R} = 800 V, Q_C = \int_0^{V_R} C(V) dV, T_{\rm J} = 25^{\circ} C$	-	97	-	nC	
Total Capacitance	С	$V_R = 0V, f = 1MHz$	-	1318	-		
		V _R = 400V,f = 1MHz	-	91	-	pF	
		V _R = 800V,f = 1MHz	-	70	-		

Thermal Characteristics

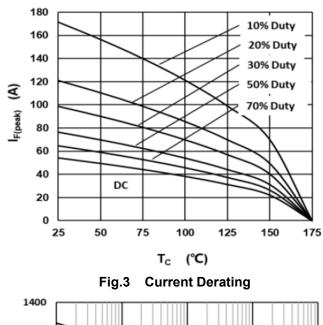
Parameter	Symbol	Min.	Тур.	Max.	Units
Thermal Resistance (Junction to Case)	$R_{ extsf{ heta}JC}$	-	0.7	-	°C/W

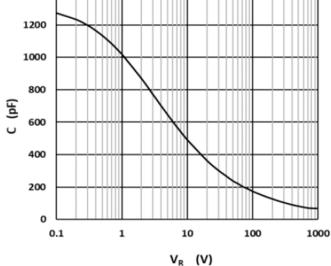
Typical Characteristics

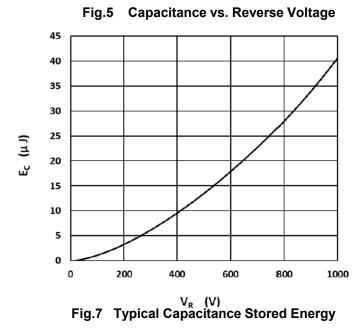


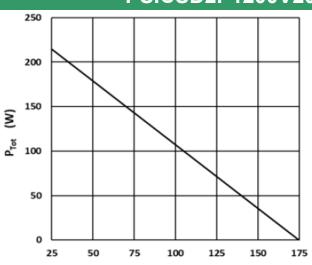
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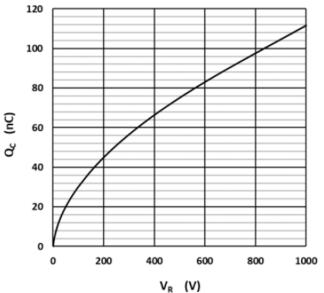


Fig.6 Capacitance Charge vs. Reverse Voltage

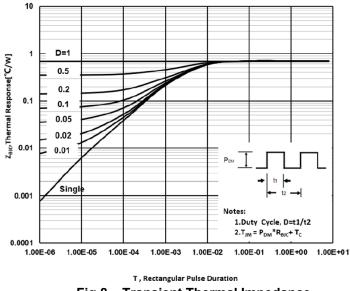
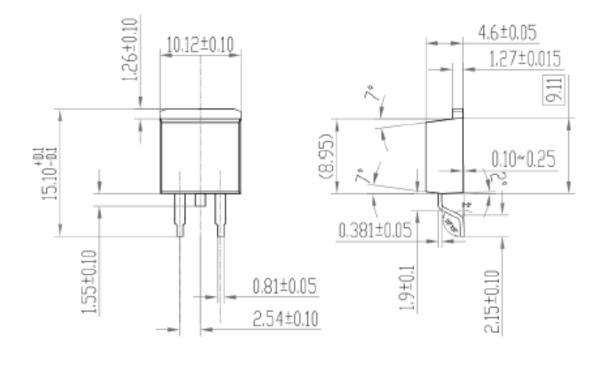


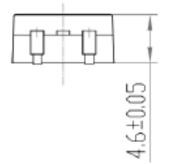
Fig.8 Transient Thermal Impedance

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Product Dimension (TO-263-2L)





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